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Amendments to the Claims:

The following listing of claims will replace any/all prior versions, and listings, of claims in the application, wherein additions are shown in underlined text and deletions are shown in strike-out text or between brackets ([]):

1. – 7. (Canceled)

8. (Currently Amended) A capacitor comprising:

a lower electrode formed on a substrate, ~~wherein the lower electrode includes~~
including a metal pattern made by a single material, a seed layer comprising Pt
between the substrate and the metal pattern, and a layer comprising Pt covering an upper surface and sidewalls of the metal pattern, ~~and wherein the metal pattern is~~
formed of a material capable of forming a conductive oxide;
a dielectric layer formed on the lower electrode; and
an upper electrode formed on the dielectric layer.

9. (Canceled)

10. (Currently Amended) The capacitor as recited in claim [9] 8, wherein the metal pattern is formed comprising a metal selected from the group consisting of Ru and Ir.

11. (Currently Amended) The capacitor as recited in claim [9] 8, wherein the seed layer comprising Pt covers sidewalls and a bottom surface of the metal pattern.